

**REPLY UNDER 37 CFR 1.116  
EXPEDITED PROCEDURE  
TECHNOLOGY CENTER 2800**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

<b>In Re Application of:</b>	William G. America	<b>Conf. No.:</b>	3775
<b>Serial No.:</b>	10/709,776	<b>Art Unit:</b>	2811
<b>Filed:</b>	5/27/2004	<b>Dkt. #:</b>	FIS920040083US1 (IBMF-0058)
<b>Title:</b>	SEMICONDUCTOR DEVICE FORMED BY IN-SITU MODIFICATION OF DIELECTRIC LAYER AND RELATED METHODS		
		<b>Examiner:</b>	Im, Junghwa M

Mail Stop AF  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**AFTER-FINAL AMENDMENT**

Sir:

**I. INTRODUCTORY COMMENTS**

This paper is being filed in response to the Office Action dated May 17, 2007. Please amend the above-referenced patent application as follows: